NIKO-SEM

P-Channel Enhancement Mode Field Effect Transistor

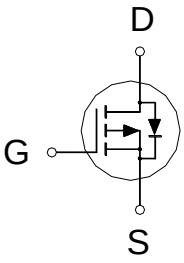
P7510EEU

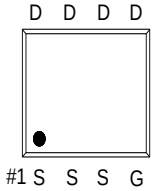
PDFN 3.3x3.3S

Halogen-Free & Lead-Free

PRODUCT SUMMARY

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
-100V	75mΩ	-13A





1. GATE
2. DRAIN
3. SOURCE

RoHS Compliant

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Drain-Source Voltage		V_{DS}	-100	V
Gate-Source Voltage		V_{GS}	±25	V
Continuous Drain Current	T_C = 25 °C	I_D	-13	A
	T_C = 100 °C		-8.2	
Pulsed Drain Current[1]		I_{DM}	-31	
Continuous Drain Current	T_A = 25 °C	I_D	-4	
	T_A = 70 °C		-3.2	
Avalanche Current		I_{AS}	-15	
Avalanche Energy	L = 1mH	E_{AS}	113	mJ
Power Dissipation	T_C = 25 °C	P_D	27	W
	T_C = 100 °C		11	
Power Dissipation[3]	T_A = 25 °C	P_D	2.6	W
	T_A = 70 °C		1.7	
Operating Junction & Storage Temperature Range		T_j, T_{stg}	-55 to 150	°C

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE		SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Ambient[2]	t ≦10s	$R_{\theta JA}$		48	°C / W
Junction-to-Ambient[2]	Steady-State	$R_{\theta JA}$		80	
Junction-to-Case	Steady-State	$R_{\theta JC}$		4.6	

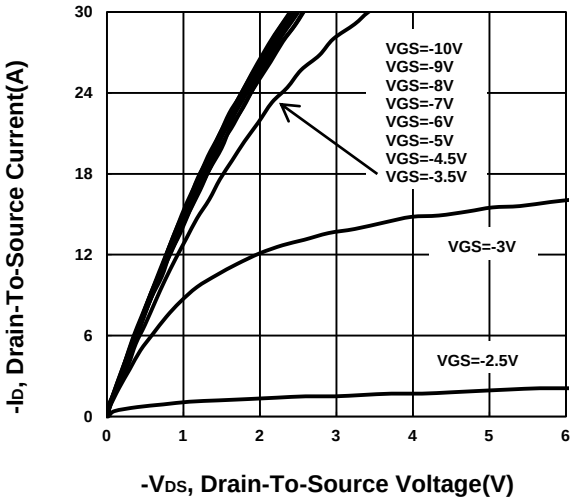
[1]Pulse width limited by maximum junction temperature.
[2]The value of $R_{\theta JA}$ is measured with the device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A =25°C.
[3]The Power dissipation is based on $R_{\theta JA}$ t ≦10s value.

ELECTRICAL CHARACTERISTICS (T_J = 25 °C, Unless Otherwise Noted)

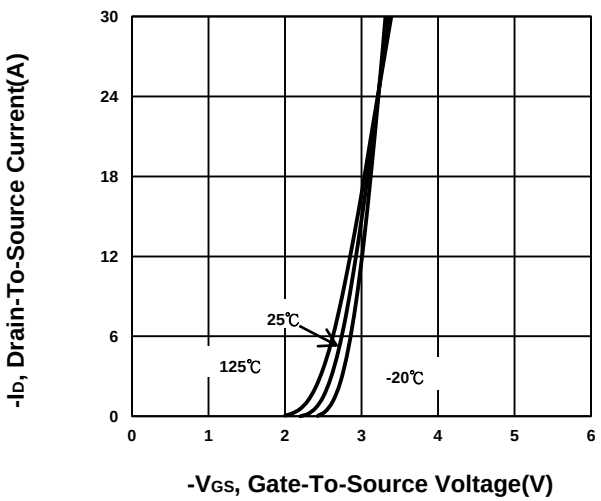
PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS MIN	LIMITS TYP	LIMITS MAX	UNIT
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = -250μA	-100			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = -250μA	-1.3	-1.8	-2.3	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0V, V_{GS} = ±25V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = -100V, V_{GS} = 0V			-1	μA
		V_{DS} = -100V, V_{GS} = 0V, T_J = 55 °C			-10	
Drain-Source On-State Resistance[1]	$R_{DS(ON)}$	V_{GS} = -4.5V, I_D = -10A		61	85	mΩ
		V_{GS} = -10V, I_D = -10A		56	75	
Forward Transconductance[1]	g_{fs}	V_{DS} = -5V, I_D = -10A		33		S
DYNAMIC						
Input Capacitance	C_{iss}	V_{GS} = 0V, V_{DS} = -50V, f = 1MHz	1370	2284	3198	pF
Output Capacitance	C_{oss}		70	118	212	
Reverse Transfer Capacitance	C_{rss}		33	84	151	
Gate Resistance	R_g	V_{GS} =0V, V_{DS} = 0V, f = 1MHz	0.1	7.7	15.4	Ω
Total Gate Charge[2]	$Q_{g\ (V_{GS}=-10V)}$	V_{DS} = -50V , V_{GS} = -10V, I_D = -10A	29	49	69	nC
	$Q_{g(V_{GS}=-4.5V)}$			25		
Gate-Source Charge[2]	Q_{gs}		3.7	6.2	12	
Gate-Drain Charge[2]	Q_{gd}		6	12	22	
Turn-On Delay Time[2]	$t_{d(on)}$	V_{DS} = -50V , I_D ≅ -10A, V_{GS} = -10V, R_{GEN} =6Ω		11		nS
Rise Time[2]	t_r			38		
Turn-Off Delay Time[2]	$t_{d(off)}$			119		
Fall Time[2]	t_f			86		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T_J = 25 °C)						
Continuous Current	I_S				-13	A
Forward Voltage[1]	V_{SD}	I_F = -10A, V_{GS} = 0V			-1.2	V
Reverse Recovery Time	t_{rr}	I_F = -10A, dI_F/dt = 100A / μS		52		nS
Reverse Recovery Charge	Q_{rr}			54		nC

[1]Pulse test : Pulse Width ≤ 300 μsec, Duty Cycle ≤ 2%.
[2]Independent of operating temperature.

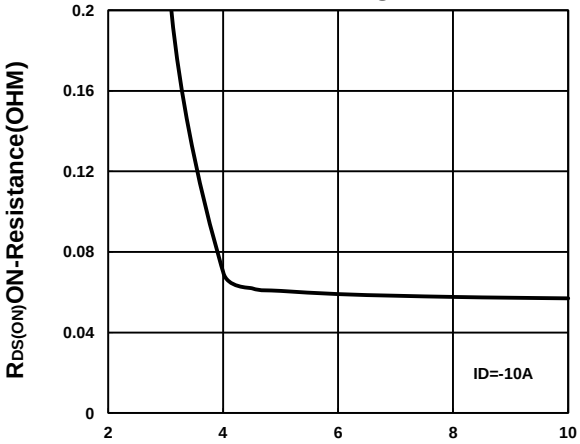
Output Characteristics



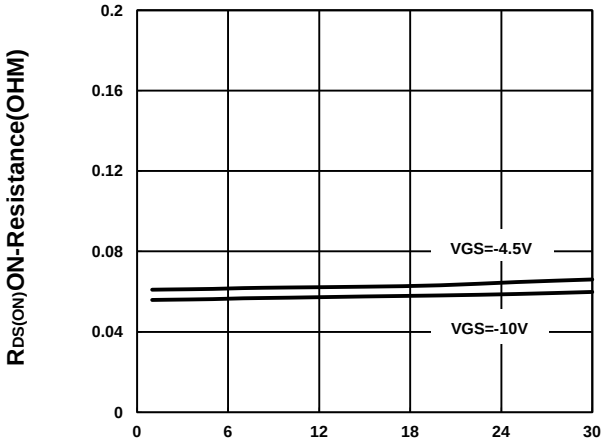
Transfer Characteristics



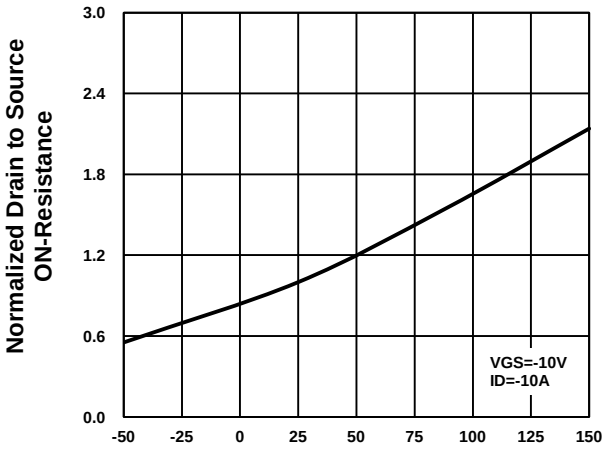
On-Resistance VS Gate-To-Source Voltage



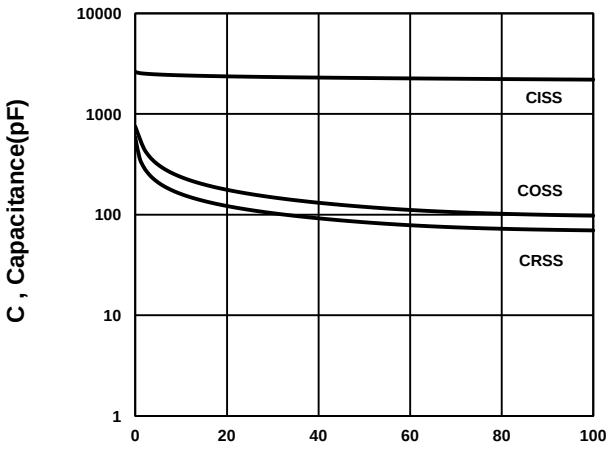
On-Resistance VS Drain Current



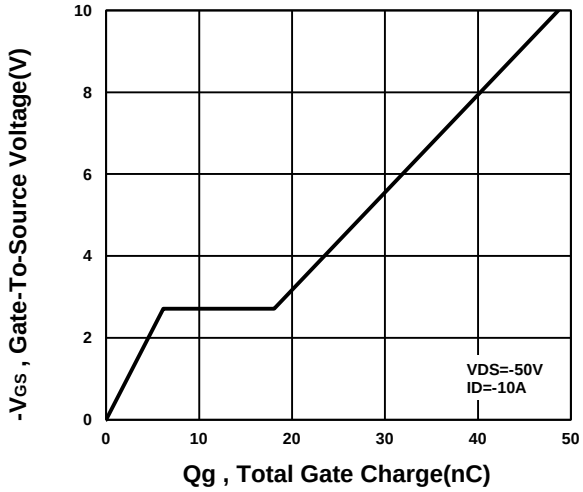
On-Resistance VS Temperature



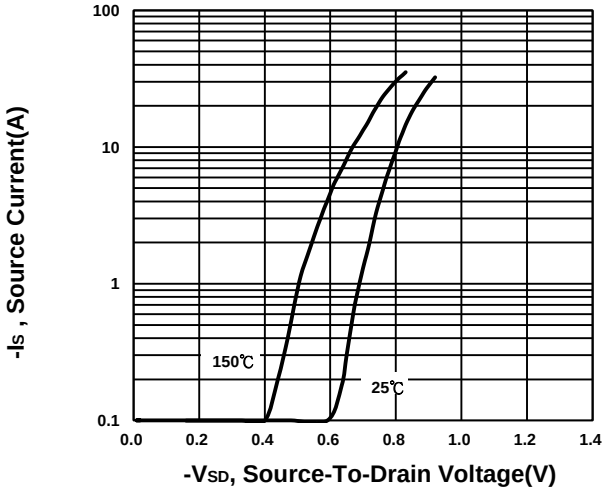
Capacitance Characteristic



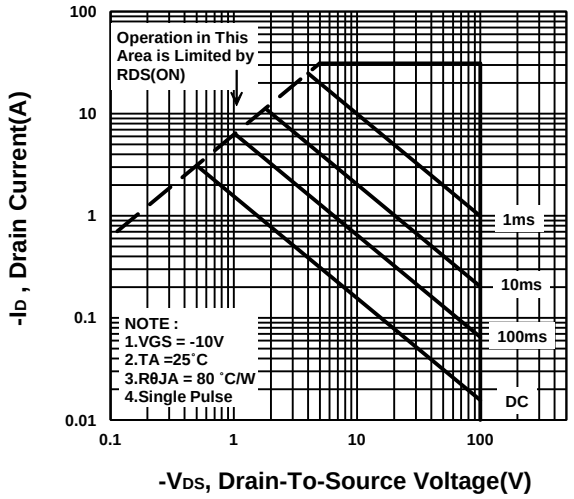
Gate charge Characteristics



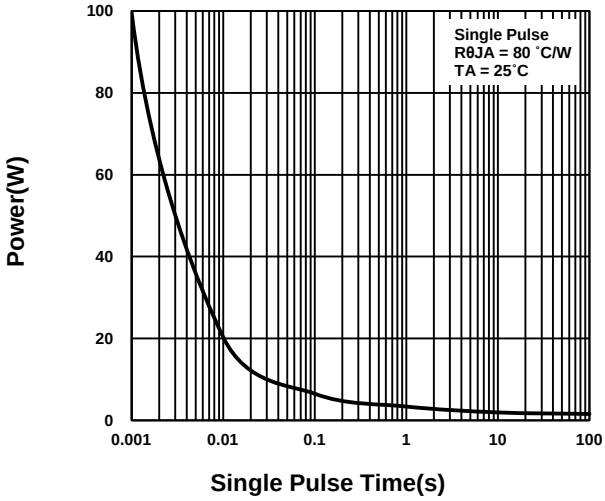
Source-Drain Diode Forward Voltage



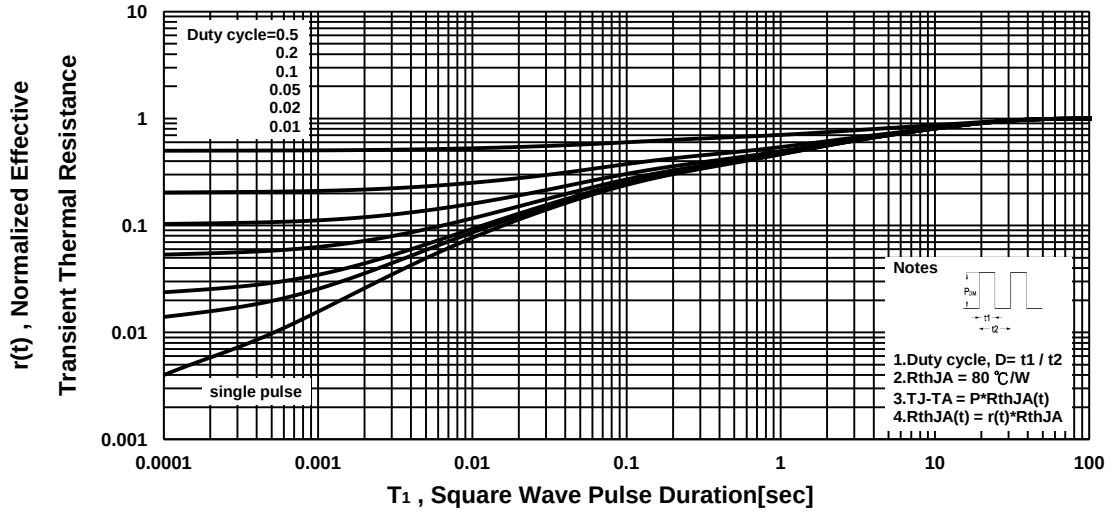
Safe Operating Area



Single Pulse Maximum Power Dissipation



Transient Thermal Response Curve



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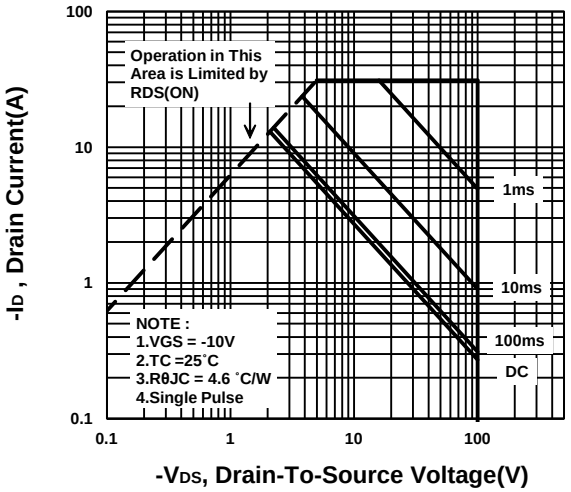

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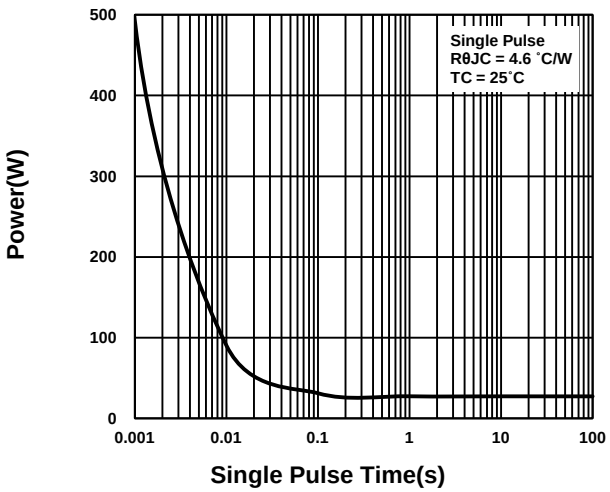

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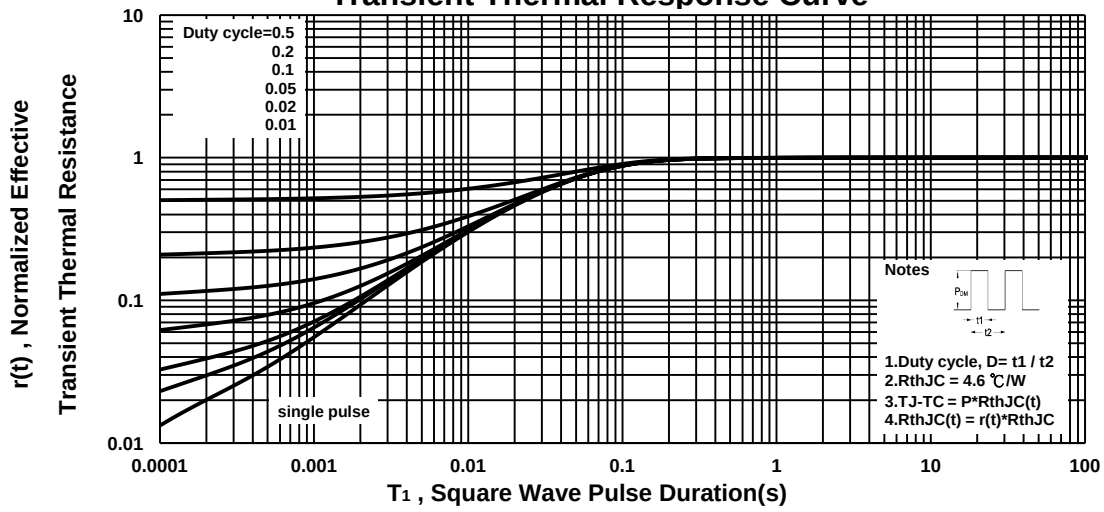
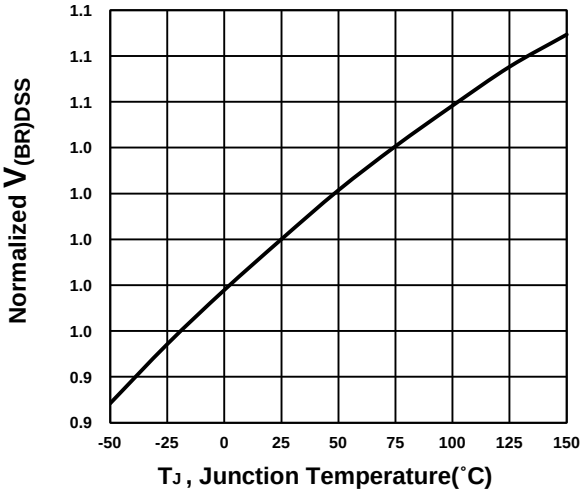


V(BR)DSS VS Temperature



VGS(th) VS Temperature